

ABSTRACT OF THE DISCLOSURE

A semiconductor substrate that suppresses not only auto doping but also warpage can be provided by disposing an oxide film (4) at a position in a semiconductor substrate (1), so as to be apart from a main surface (1a) and a reverse surface (1b). The oxide film (4) can be so disposed that it is apart not less than 200 nm from the reverse surface (1b), and extends throughout the semiconductor substrate (1) in a thickness of 400 to 1000 nm, by implanting oxygen ion from the reverse surface (1b), followed by annealing.